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| Application Number | 10/602,436 | | | | |
| Filing Date | 06-23-03 | | | | |
| First Named Inventor | Jong-Jan Lee | | | | |
| Art Unit | 281 | | | | |
| Examiner Name | H- VU | | | | |
| Altorney Docket Number | SLA0733 | | | | |

| | | | U.S. PATE | NT DOCUMENTS_ | |
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| Examiner Initials | | Document Number | Publication Date: | Name of Palentee or Applicant of Cited Document | Pages: Columns: Lines, Where Relevant Passages or Relevant Figures Appear |
| V | | Us- 6,413,802 B1 | 07-02-2002 | Hu et al. | Comments of the Comments of th |
| | | US- 6,432,829 B2 | 08-13-2002 | Muller et al. | THE RESIDENCE AND ADDRESS OF THE PARTY OF TH |
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| | | us- 5,241,197 | 08-31-1993 | Murakami et al. | |
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| | | OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS | |
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| Examilner Initials | Cite No. 1 | include name of: the author (in CAPITAL:LETTERS), title of the article (when appropriate); title of the lemi(book; magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue; number(s), nublisher, city and/or country where published. | 7 |
| June (1977) and the state (1977) as | America escreta | N. SUGIYAMA, T. MIZUNO, S. TAKAGI, M. KOIKE, A. KUROBE, Formation of strained-silicon layer on thin relaxed SiGe/SiO-/Si structure using SIMOX technology, Thin Solid Films, 396 (2000) 199-202. M.T. CURRIE, C.W. LEITZ, T.A. LANGDO, G. TARASCHI, E.A. FITZGERALD, D.A. ANTONIADIS, Carrier mobilities and process stability of strained Si n- and p- MOSFETs | The second secon |
| entere per en | gada o ellen | on SiGe virtual substrate, J. Vac. Sci. Technol. B 19 (6), Nov/Dec 2001, pp 2268-2279. T. TEZUKA, N. SUGIYAMA, T. MIZUNO, S. TAKAGI, High performance strained-Sion-insulator MOSFETs by novel fabrication processes utilizing Ge-condensation technique, 2002 Symposium on VLSI Technology, Digest of Technical paper. | |
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| and and a first of | | insulator substrates, Thin Solid Films, 321 (1998) 245-250. X. HUANG, W-C. LEE, C. KUO, D. HISAMOTO, L. CHANG, J. KEDZIERSKI, E. ANDERSON, H. TAKEUCHI, Y-K. CHOI, K. ASANO, V. SUBRAMANIAN, T-J. KING, J. BOKOR, C. HU, Sub 50-nm finFET: PMOS, IEDM-Tech. Dig., p. 67-70, 1999. | , (). (). |
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| . Yı | ande t | Y-K. CHOI, N. LINDERT, P. XUAN, S. TANG, D. HA, E. ANDERSON, T-J. KING, J. BOKOR, C. HU, Sub-20 nm CMOS finFET technologies, IEDM Tech. Dig., 2001. | -50 |
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